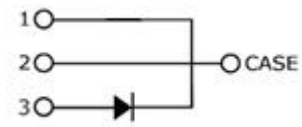
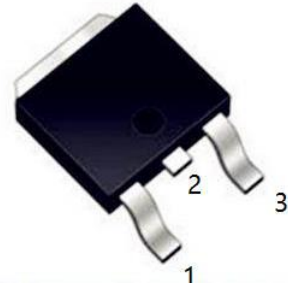


V_{RRM} = 650 V
 $I_F(T_c=150^{\circ}C)$ = 6.3 A
 Q_C = 19.5 nC

Features:

- Extremely low reverse current
- No reverse recovery current
- Temperature independent switching
- Positive temperature coefficient on V_F
- Excellent surge current capability
- Low Capacitive charge



Benefits

- Essentially No switching losses
- System efficiency improvement over Si Diodes
- Increased power density
- Enabling higher switching frequency
- Reduction of Heat Sink Requirements
- System Cost savings due to smaller magnetics
- Reduced EMI



Applications

- Switch Mode Power Supplies (SMPS)
- Uninterruptable power supplies
- Motor Drivers
- Power Factor Correction

Pacakge Pin definitions

- Pin1-Cathode
- Pin2-Cathode
- Pin3-Anode

Package Parameters

Part Number	Marking	Package
B1D06065E	B1D06065E	TO-252-3L

Maximum ratings

Symbol	Parameter	Test conditions	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage		650	V
V_{RSM}	Surge Peak Reverse Voltage		650	V
I_F	Continuous Forward Current	$T_c=25^{\circ}C$ $T_c=135^{\circ}C$ $T_c=150^{\circ}C$	18 8.4 6.3	A
I_{FSM}	Non-Repetitive Forward Surge Current	$T_c=25^{\circ}C$, $t_p=10ms$, sine halfwave	48	A
$\int i^2 dt$	i^2t Value	$T_c=25^{\circ}C$, $t_p=10ms$	11.5	A ² S
P_{tot}	Power Dissipation	$T_c=25^{\circ}C$ $T_c=110^{\circ}C$	72 31	W
T_j	Operating junction temperature		-55~175	$^{\circ}C$
T_{stg}	Storage temperature		-55~135	$^{\circ}C$

Thermal Characteristics

Symbol	Parameter	Value			Unit
		Min.	Typ.	Max.	
$R_{th(jc)}$	Thermal resistance from junction to case		2.065		K/W
$R_{th(ja)}$	Thermal resistance from junction to ambient		109.1		K/W

Electrical Characteristics
Static Characteristics (T_j=25°C unless otherwise specified)

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
V _{DC}	DC blocking voltage	T _j =25°C	650			V
V _F	Diode forward voltage	I _F =6A T _j =25°C I _F =6A T _j =175°C		1.45 1.9		V
I _R	Reverse current	V _R =650V T _j =25°C V _R =650V T _j =175°C		0.05 3		μA

Dynamic Characteristics (T_j=25°C unless otherwise specified)

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
Q _C	Total capacitive charge	V _R =400V T _j =25°C $Q_c = \int_0^{V_R} C(V)dV$		19.5		nC
C	Total Capacitance	V _R =1V f=1MHz V _R =300V f=1MHz V _R =600V f=1MHz		290 33.7 33.2		pF

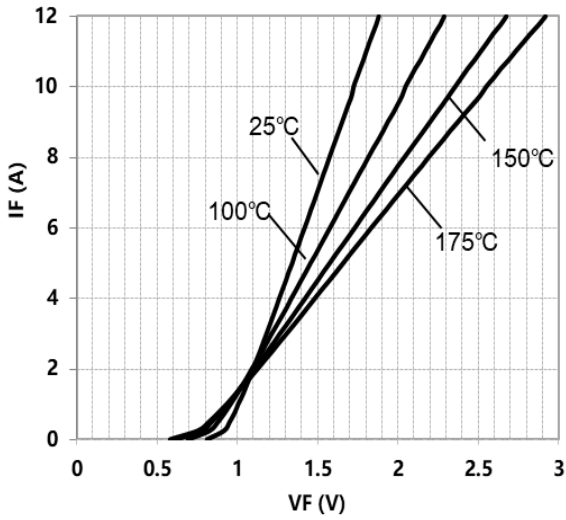


Figure 1. Typical forward characteristics

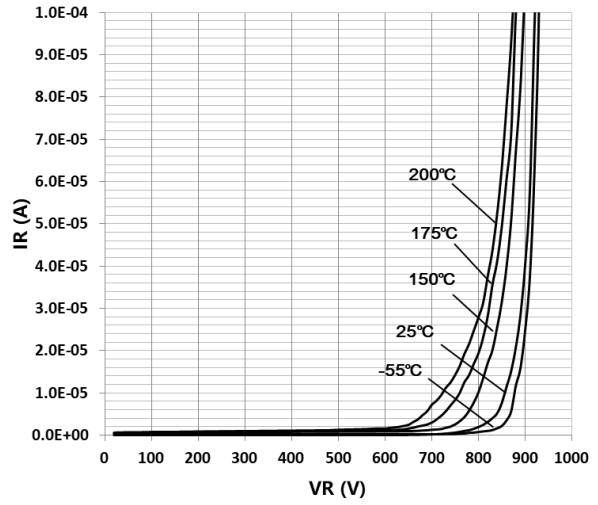


Figure 2. Typical reverse current as function of reverse voltage

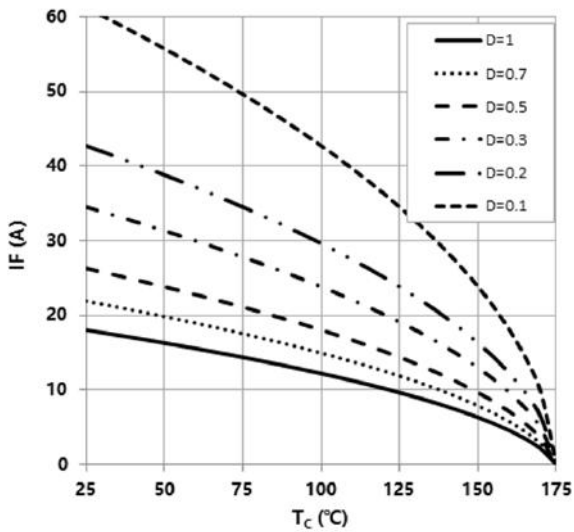


Figure 3. Diode forward current as function of temperature, D=duty cycle

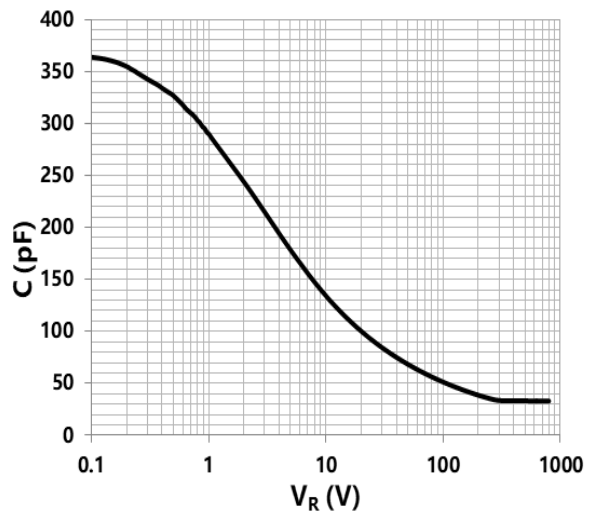


Figure 4. Typical capacitance as function of reverse voltage, $C=f(V_R)$; $T_j=25^\circ\text{C}$; $f=1\text{ MHz}$

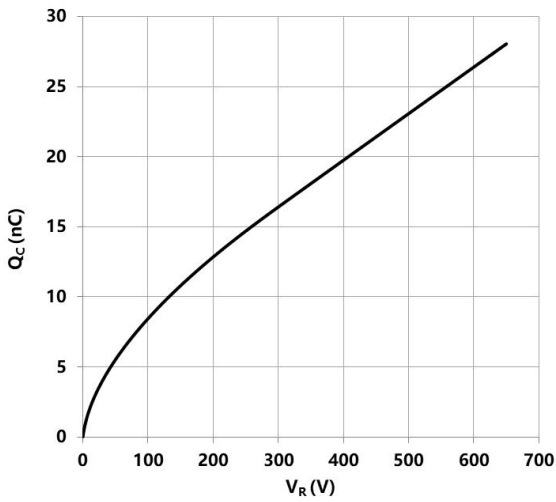


Figure 5. Typical reverse charge as function of reverse voltage

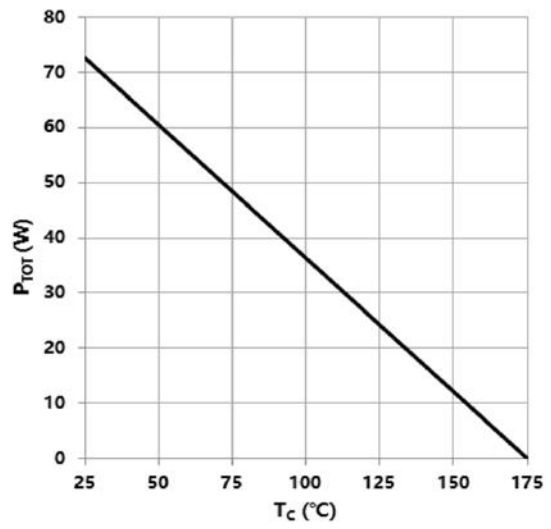


Figure 6. Power dissipation as function of case temperature

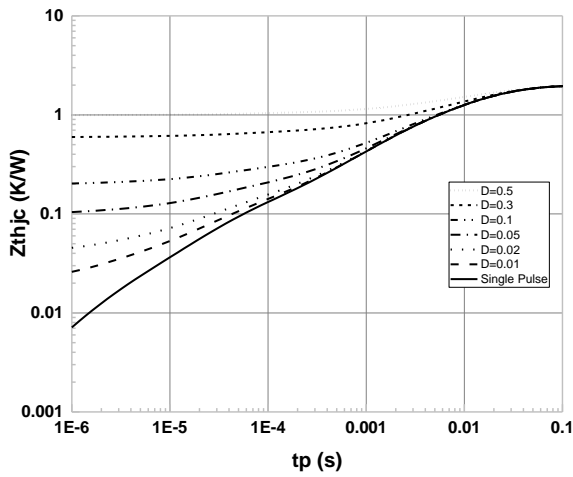
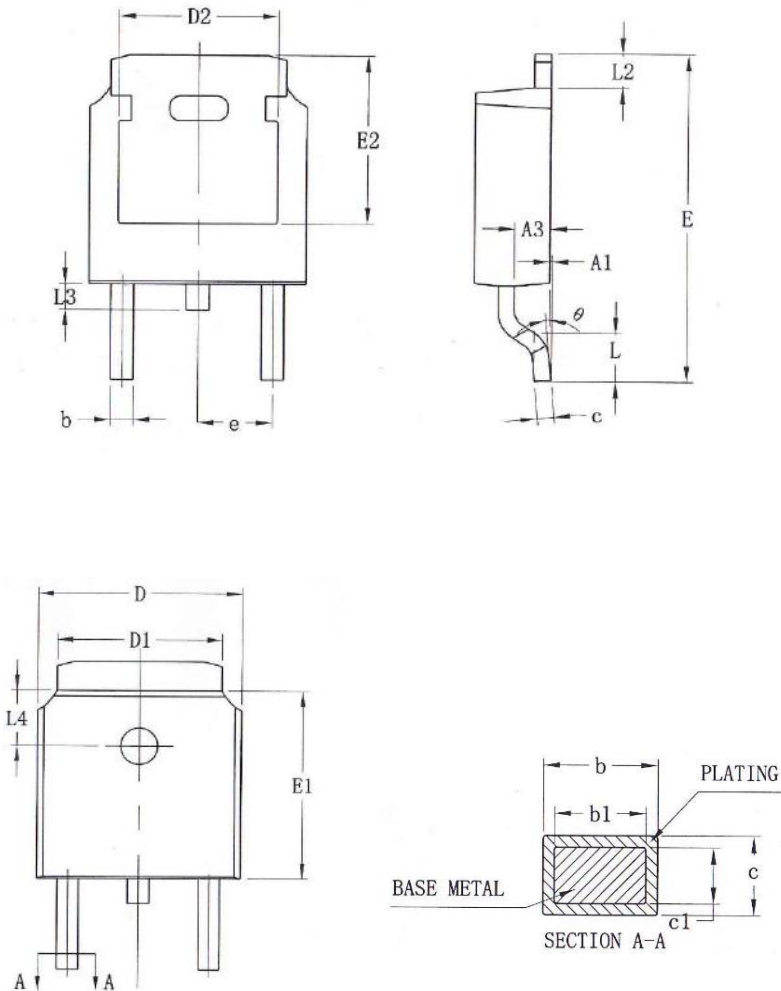


Figure 7. Max. transient thermal impedance, $Z_{th,jc}=f(t)$, parameter: $D=t/T$

Package Dimensions



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A1	0.00	—	0.10
A2	2.20	2.30	2.40
A3	1.02	1.07	1.12
b	0.74	—	0.82
b1	0.73	0.76	0.79
c	0.51	—	0.55
c1	0.50	0.51	0.52
D	6.50	6.60	6.70
D1	5.33REF		
D2	4.83REF		
E	9.90	10.10	10.30
E1	6.00	6.10	6.20
E2	5.30REF		
e	2.286BSC		
L	1.40	1.50	1.60
L2	0.90	—	1.25
L3	0.60	0.80	1.00
L4	1.70	1.80	1.90
θ	0		8°

Revision History:

2019-05-30,Rev.1.0

Previous Revision:

Rev.1.0 Release of datasheet

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